

ABSTRACT

There is provided an Al wiring material which can achieve sufficient bond reliability of bonded parts in a high-temperature environment at the time when a semiconductor device operates. The Al wiring material containing one or more of Pd and Pt so as to satisfy

$$3 \leq x1a \leq 90 \text{ or } 10 \leq x1b \leq 250, \text{ and}$$
$$3 \leq (x1a + x1b) \leq 300,$$

where x1a and x1b are respectively a content of Pd [mass ppm] and a content of Pt [mass ppm], with the balance comprising Al, and an average crystal grain diameter on a cross-section perpendicular to a longitudinal direction of the Al wiring material is 3 to 35 μm .

[No figure]